Form PTO-1	1449	Docket Number (Option	Application Number				
INFORI	MATION DISCI IN AN APPL	LOSURE CIT	Applicant Wang et al.				
(Use several sheets if necessary)				Filing Date July 14, 2003 Group Art Unit Unknown			
<u>م الدي يا گاميداً قام يا د.</u> در	and the second of the second	ra water in the	ter jeden tolj	A second second	Liza Sanc V.	Gloup Art	2823
and the same	A Secretarial Control of the Secretarian	U.S.	PATENT	DOCUMENTS	. (3) . v.		
EXAMINER INITIAL	DOCUMENT NUMBER	DATE		NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
me.	4,491,860	01/1985	Lim		100		
Me_	4,740,485	04/1988	Sharpe-Ge	isler		3 3 3 3 3 3 3 3 3 3 3 3 3 3 3 3 3 3 3 3	- Ta
	4,783,424	04/1997	Ohno et al.	The same of the sa	÷ .	-	
me.	4,796,075	01/1989	Whitten	والمراجع وا		1	
CMY.	5,589,706	12/1996	Mitwalsky e	et al.	1. 1. 1. 1. 1. 1. 1. 1. 1. 1. 1. 1. 1. 1		
ME)	5,618,750	04/1997	Fujuhara e	t al.		-,	
MB)	5,625,218	04/1997	Yamadera	et al.			
AND.	5,914,524	06/1999	Komenaka				
MB	5,990,537	11/1999	Endo et al.	Y			
Me	6,277,674 B1	08/2001	Wang et al.		<u>A. 3.18.</u>		*
				<u> </u>	<u> </u>	<u> </u>	
Justine at the		FOREIG	N PATEN	T DOCUMENTS		41, 41, 41, 41, 41, 41, 41, 41, 41, 41,	124 4 4 4 4 4 4 4 4 4 4 4 4 4 4 4 4 4 4
	Carron W. Land C. A. C. Carro				Translation		
<u> </u>	LOCUMENT NUMBER	DATE	1,000	COUNTRY	CLASS	SUBCLASS	YES NO
		last and the second			1		n .
		and the state of t		the second of th		iario € Ngiling	
<u>vaidandai.</u>		Secretary and the		A Alexander			
<u> a silite e e e e e e e e e e e e e e e e e e </u>		nger (n. 19. <u>1982) in komplikat de Millerde</u>				ر آن المدر الرحال المدرور	
	an Takan Samakan da Labaran Sama		August Aug		ราม ก็การ เมื่อสมอ เรียร์		
	est to be over the same of	01	HER DOC	UMENTS	(Including A	Author Title Date	, Pertinent Pages, Etc.
100	7.	· ×		an seamh a a sui a beist a	(modes g	toulor, Title, Date	, returent rages, Etc.
11111							
719/	Fukuda, Y	ukio, et al., <u>A Ne</u> olysilicon. IEEE	w Fusible-Ty	pe Programmable Ele	ment Comp	osed of Alu	minum and
714	Fukuda, Y P	ukio, et al., <u>A Ne</u> olysilicon. IEEE	w Fusible-Ty Transactions	pe Programmable Ele on Electron Devices,	ment Comp Vol. ED-3	osed of Alu 3, No. 2, Fe	<u>ıminum and</u> b. 1986.
119	Fukuda, Y P	ukio, et al., <u>A Ne</u> olysilicon. IEEE	w Fusible-Ty Transactions	pe Programmable Ele on Electron Devices,	ment Comp Vol. ED-3	oosed of Alu 3, No. 2, Fe	<u>ıminum and</u> b. 1986.
114	Fukuda, Y	ukio, et al., <u>A Ne</u> olysilicon. IEEE	w Fusible-Ty Transactions	pe Programmable Ele on Electron Devices,	ment Comp Vol. ED-3	oosed of Alu 3, No. 2, Fe	<u>ıminum and</u> b. 1986.
714	Fukuda,.Y	ukio, et al., <u>A Ne</u> Polysilicon. IEEE	w Fusible-Ty Transactions	pe Programmable Ele on Electron Devices,	ment Comp Vol. ED-3	oosed of Alu 3, No. 2, Fe	ıminum and b. 1986.
914	Fukuda, Y	ukio, et al., <u>A Ne</u>	w Fusible-Ty Transactions	pe Programmable Ele on Electron Devices,	ment Comp Vol. ED-3	oosed of Alu 3, No. 2, Fe	iminum and b. 1986.
AMINER	P and a substitute of the subs	olysilicon. IEEE	Transactions	pe Programmable Ele on Electron Devices,	went Comp Vol. ED-3	oosed of Alu 3, No. 2, Fel	iminum and b. 1986.
AMINER:	P	ukio, et al., <u>A Ne</u> Polysilicon. IEEE	Transactions	on Electron Devices,	went Comp Vol. ED-3	oosed of Alu 3, No. 2, Fe	iminum and b. 1986.